



DMP3045LFVWQ

Product Summary

BV _{DSS}	Rds(on) Max	I _D Max Tc = +25°C		
2014	42mΩ @ V _{GS} = -10V	-19.9A		
-30V	65mΩ @ V _{GS} = -4.5V	-16A		

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power management functions
- DC-DC converters

30V P-CHANNEL ENHANCEMENT MODE MOSFET

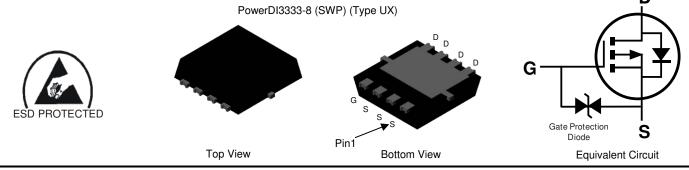
Features and Benefits

- Low RDS(ON) Ensures On-State Losses Are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DIODES[™] DMP3045LFVWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/guality/product-definitions/

Mechanical Data

- Package: PowerDI[®]3333-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over copper Leadframe. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.072 grams (Approximate)



Ordering Information (Note 4)

Part Number	Bookogo	Packing		
Part Nulliber	Package	Qty.	Carrier	
DMP3045LFVWQ-7	PowerDI3333-8 (SWP) (Type UX)	2,000	Tape & Reel	
DMP3045LFVWQ-13	PowerDI3333-8 (SWP) (Type UX)	3,000	Tape & Reel	

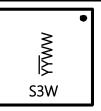
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\frac{S3W}{YY} = Product Type Marking Code$ $\frac{YY}{YW} = Date Code Marking$ $\frac{YY}{YY} = Last Two Digits of Year (ex: 22 = 2022)$ WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	-30	V		
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) VGS = -10V	Steady State	T _A = +25°C T _A = +70°C	ID	-5.7 -4.6	A
Continuous Drain Current (Note 7) V _{GS} = -10V	Steady State	Tc = +25°C Tc = +70°C	ID	-19.9 -15.9	А
Maximum Continuous Body Diode Forward Current (Note 7)			Is	-1.3	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			ldм	-76	А
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	-76	А
Avalanche Current (Note 8) L = 1mH			las	-7.8	Α
Avalanche Energy (Note 8) L = 1mH			Eas	30.8	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	TA = +25°C	PD	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	135	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	61	°C/W
Thermal Resistance, Junction to Case (Note 7)	Rejc	5	°C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BVDSS	-30	—		V	$V_{GS} = 0V, I_D = -250 \mu A$	
Zero Gate Voltage Drain Current	IDSS		—	-1	μA	$V_{DS}=-24V,V_{GS}=0V$	
Gate-Source Leakage	IGSS		—	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	—	-2.1	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance		—	25	42	mΩ	$V_{GS} = -10V, I_{D} = -4.9A$	
Static Drain-Source On-Resistance	RDS(ON)		43	65	11177	V _{GS} = -4.5V, I _D = -3.7A	
Diode Forward Voltage	Vsd	—	-0.7	-1.2	V	$V_{GS} = 0V$, $I_S = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss		782		pF		
Output Capacitance	Coss		110	—	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss		74	_	pF		
Gate Resistance	Rg	—	10.4	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg		6.6	_	nC		
Total Gate Charge (V _{GS} = -10V)	Qg		13.6	_	nC		
Gate-Source Charge	Qgs		2.1	_	nC	V _{DS} = -15V, I _D = -4.9A	
Gate-Drain Charge	Qgd	_	2.7	_	nC		
Turn-On Delay Time	td(on)		4.1	_	ns		
Turn-On Rise Time	t _R		6.1	_	ns	$V_{DD} = -15V, V_{GS} = -10V,$	
Turn-Off Delay Time	tD(OFF)		24.6	_	ns	$I_{D} = -4.9A, R_{G} = 6\Omega$	
Turn-Off Fall Time	tF		13.1		ns		
Reverse Recovery Time	trr		12.7		ns		
Reverse Recovery Charge	Qrr		4.8	_	nC	Is = -11.5A, dl/dt = 100A/µs	

Notes:

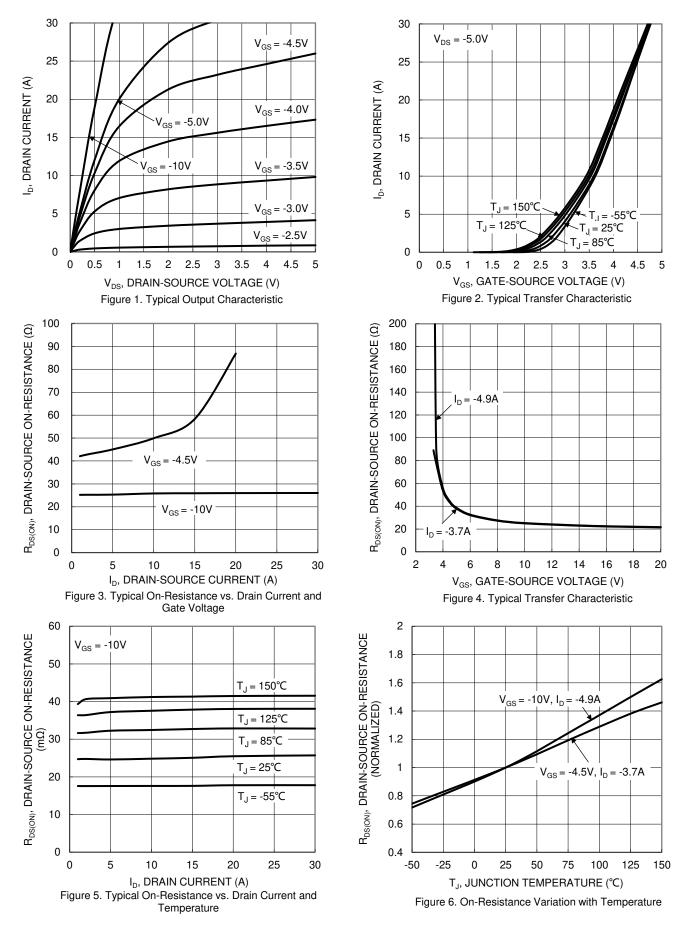
Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

7. Thermal resistance from junction to soldering point (on the exposed drain pad). 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

9. Short duration pulse test used to minimize self-heating effect.

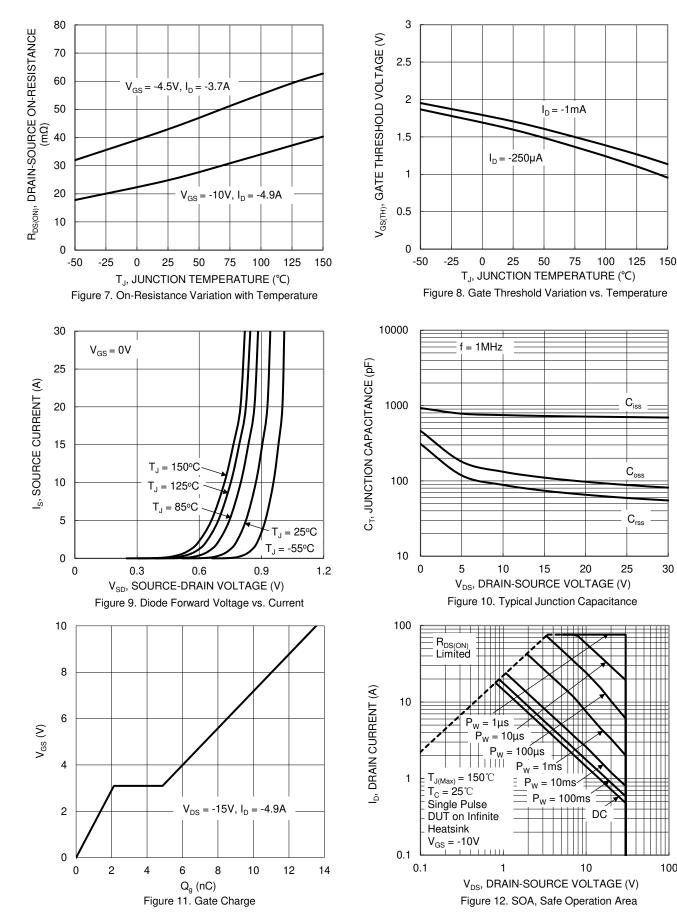
10. Guaranteed by design. Not subject to product testing.





DMP3045LFVWQ Document number: DS43270 Rev. 5 - 2





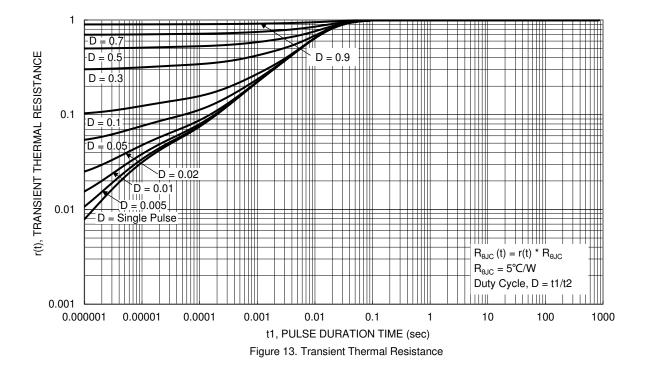
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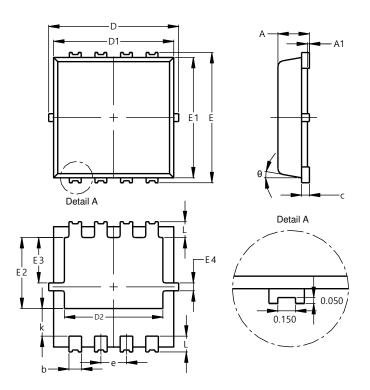






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



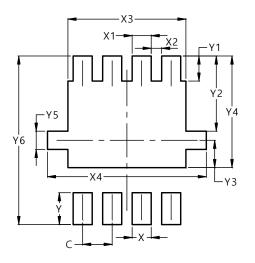
PowerDI3333-8 (SWP)							
	(Type UX)						
Dim	Min	Max	Тур				
Α	0.75	0.85	0.80				
A1	0.00	0.05					
b	0.25	0.40	0.32				
C	0.10	0.25	0.15				
D	3.20	3.40	3.30				
D1	2.95	3.15	3.05				
D2	2.30	2.70	2.50				
ш	3.20	3.40	3.30				
E1	2.95	3.15	3.05				
E2	1.60	2.00	1.80				
E3	0.95	1.35	1.15				
E4	0.10	0.30	0.20				
e	_	_	0.65				
k	0.50	0.90	0.70				
L	0.30	0.50	0.40				
θ	0°	12°	10°				
All I	Dimens	sions ir	n mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)			
С	0.650			
Х	0.420			
X1	0.420			
X2	0.230			
X3	2.600			
X4	3.500			
Y	0.700			
Y1	0.550			
Y2	1.650			
Y3	0.600			
Y4	2.450			
Y5	0.400			
Y6	3.700			



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